

Docket No. 1232-5237

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

App	licant(	(s)	۱:

A. KURIYAMA, et al.

Group Art Unit:

2812

Serial No.:

10/735,062

Examiner:

E. PERT

Filed:

December 11, 2003

For:

SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

## INFORMATION DISCLOSURE STATEMENT

P.O. E	Stop nissioner for Patents Box 1450 ndria, VA 22313-1450
Sir:	
refere	Pursuant to Rule 56, applicant hereby calls the attention of the Patent Office to the nees listed on the attached Form PTO 1449.
Copy(	ies) of these references:
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	Were filed in related application U.S. Serial No(s) , filed , respectively.
	This document is being filed within three (3) months of the filing date of the application
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	This document is being concurrently filed with the above-identified application
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X	The Commissioner is hereby authorized to charge any additional fees which may be required for this Information Disclosure Statement, or credit any overpayment to Deposit Account No. <u>13-4500</u> , Order No. <u>1232-5237</u> . A DUPLICATE COPY OF THIS SHEET IS ATTACHED.
	Respectfully submitted,  MORGAN & FINNEGAN, LAT.P.

Dated: February 7, 2006

Eric G. Wright

Registration No. 48,045

Correspondence Address:

MORGAN & FINNEGAN, L.L.P. 3 World Financial Center New York, NY 10281-2101 (212) 415-8700 Telephone (212) 415-8701 Facsimile

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**FORM PTO-1449A** 

INFORMATION DISCLOSURE CITATION

Attorney Docket:	Se
1232-5237	10

Serial No.: 10/735,062

Applicant:

A. KURIYAMA, et al.

Filing Date: December 11, 2003

Group Art Unit: 2812

## U.S. PATENT / PUBLICATION DOCUMENTS

Examiner Initial		Patent/Publication Number	Publication/Issue Date	Name	Filing Date
	1.	US 2005-0053773 A1	03-10-2005	Fukutani	
	2.	US 2004-0043208 A1	03-04-2004	Fukutani	
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	12.	2001-261376 A	09-26-2001	Japan	⊠ Yes	Abstract o
	13.	2001-162600	06-19-2001	Japan	⊠ Yes	Abstract
•	14.	10-321834	12-04-1998	Japan	⊠ Yes	Abstract
	15.	H09-157062 A	06-17-1997	Japan	⊠ Yes	Abstract
	16.	WO 03/078688	09-25-2003	WIPO	⊠ Yes	Abstract
	17.	WO 03/078687	09-25-2003	WIPO	⊠ Yes	Abstract
	18.	WO 03/078685	09-25-2003	WIPO	⊠ Yes	Abstract
-	19.	WO 03/069677	08-21-2003	WIPO	⊠ Yes	N/A

Examiner		Date Considered
EXAMINER:	Initial if reference considered, whether or not citation is in conformal through citation if not in conformance and not considered copy of this form with next communication to Application	lered.

FORM PTO-1449B

INFORMATION DISCLOSURE

CITATION

		1 4 5 0 1 0
Attorney Docket:	Serial No.:	
1232-5237	10/735,062	
Applicant:		
A. KURIYAMA, et al.		
Filing Date:	Group Art Unit:	
December 11 2003	2812	

NON PATENT LITERATURE DOCUMENTS  Examiner Initials*  Cite No. Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.  RC. Furneaux, et al., The formation of controlled-porosity membranes from anodically oxidized aluminum; Nature, Vol. 333, p. 147, (1989)  2. Masuda, "Solid-state Physics", Vol. 31, p. 493, (1996)  X. Duan, et al., Indium Phosphide nanowires as building blocks for nanoscale electronic and optoelectronic devices; Nature, Vol. 409, p. 66, (2001)  M. Jacobs, et al., Unbalanced magnetron sputtered Si – A1 Coatings: plasma conditions and film properties versus sample bias voltage; Surface and Coatings Technology, 116-119  (1999) pp. 735-741  C. D. Adams, et al., Transition from lateral to transverse phase separation during film codeposition; Appl. Phys. Lett., 59 (20), 11 November 1991, 2535-2537  M. Atzmon, et al; Phase separation during film growth; J. Appl. Phys. 72 (2), 15 July 1992, 442-446  C. D. Adams, et al., Monte Carlo simulation of phase separation during thin-film codeposition; J. Appl. Phys. 74 (3), 1 August 1993, 1707-1715  C. D. Adams, et al; Phase separation during co-deposition of A1-Ge thin films; J. Mat Phys. Vol. 7, No. 3, p. 653-666 (1992)  9. 10. 11. 12. 12. 13. 14. 15. 15.			December 11, 2003 2812
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Signature	Considered	

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